

MSC70SM120JCU2
Datasheet
Boost Chopper SiC MOSFET Power Module

January 2020



a  **MICROCHIP** company

Contents

Revision History.....	1
1.1 Revision 1.0.....	1
Product Overview.....	2
2.1 Features.....	3
2.2 Benefits.....	3
2.3 Applications.....	3
Electrical Specifications.....	4
3.1 SiC MOSFET Characteristics.....	4
3.2 SiC Chopper Diode Ratings and Characteristics.....	6
3.3 Thermal and Package Characteristics.....	6
3.4 SiC MOSFET Performance Curves.....	7
3.5 SiC Diode Performance Curves.....	10
4 Package Specifications.....	11
4.1 Package Outline Drawing.....	11

1 Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision 1.0

Revision 1.0 was published in January 2020. It is the first publication of this document.

2 Product Overview

The MSC70SM120JCU2 device is a 1200 V, 89 A full Silicon Carbide power module.

Figure 1 • Electrical Schematic of MSC70SM120JCU2 Device

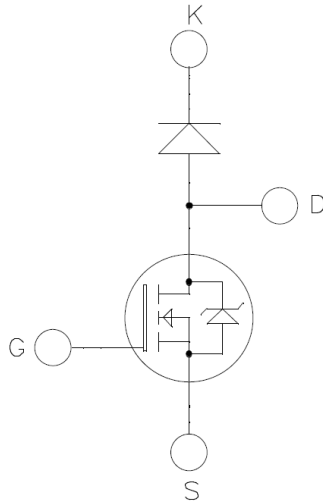
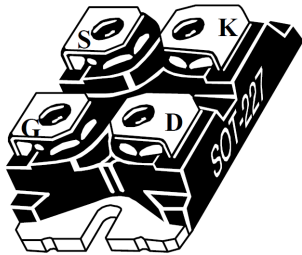


Figure 2 • SOT-227 Pinout Location



All ratings at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

2.1 Features

The following are the features of MSC70SM120JCU2 device:

- SiC power MOSFET
 - Low $R_{DS(on)}$
 - High temperature performance
- SiC Schottky diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF

2.2 Benefits

The following are the benefits of MSC70SM120JCU2 device:

- High efficiency converter
- Very low stray inductance
- Outstanding performance at high frequency operation
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

2.3 Applications

The following are the applications of MSC70SM120JCU2 device:

- AC and DC motor control
- Switched mode power supplies
- Power factor correction
- Brake switch

3 Electrical Specifications

This section provides the electrical specifications for the MSC70SM120JCU2 device.

3.1 SiC MOSFET Characteristics

The following table shows the absolute maximum ratings of MSC70SM120JCU2 device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameters	Maximum Ratings	Unit
V_{DSS}	Drain–source voltage	1200	V
I_D	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$	89 ¹
		$T_C = 80\text{ }^\circ\text{C}$	71 ¹
I_{DM}	Pulsed drain current	180	
V_{GS}	Gate–source voltage	–10/25	V
$R_{DS(on)}$	Drain–source ON resistance	31	m Ω
P_D	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$	395

Note:

1. Specification of SiC MOSFET device but output current must be limited due to size of power connectors.

The following table shows the electrical characteristics of MSC70SM120JCU2 device.

Table 2 • Electrical Characteristics

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$; $V_{DS} = 1200\text{ V}$		10	100	μA
$R_{DS(on)}$	Drain–source on resistance	$V_{GS} = 20\text{ V}$ $I_D = 40\text{ A}$	$T_C = 25\text{ }^\circ\text{C}$	25	31	m Ω
			$T_C = 175\text{ }^\circ\text{C}$	40		
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$	1.8	2.8		V
I_{GSS}	Gate–source leakage current	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$			150	nA

The following table shows the dynamic characteristics of MSC70SM120JCU2 device.

Table 3 • Dynamic Characteristics

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}$ $V_{DS} = 1000\text{ V}$ $f = 1\text{ MHz}$		3020		pF
C_{oss}	Output capacitance			270		
C_{rss}	Reverse transfer capacitance			25		
Q_g	Total gate charge	$V_{GS} = -5/20\text{ V}$ $V_{BUS} = 800\text{ V}$ $I_D = 40\text{ A}$		232		nC
Q_{gs}	Gate–source charge			41		
Q_{gd}	Gate–drain charge			50		
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5/20\text{ V}$ $V_{BUS} = 600\text{ V}$ $I_D = 50\text{ A}$ $R_{Gon} = 8\ \Omega$ $R_{Goff} = 4.7\ \Omega$		30		ns
T_r	Rise time			30		
$T_{d(off)}$	Turn-off delay time			50		
T_f	Fall time			25		
E_{on}	Turn on energy	Inductive Switching $V_{GS} = -5/20\text{ V}$ $V_{BUS} = 600\text{ V}$ $I_D = 50\text{ A}$ $R_{Gon} = 8\ \Omega$ $R_{Goff} = 4.7\ \Omega$	$T_j = 150^\circ\text{C}$	0.99		mJ
E_{off}	Turn off energy		$T_j = 150^\circ\text{C}$	0.66		mJ
R_{Gint}	Internal gate resistance			0.88		Ω
R_{thJC}	Junction-to-case thermal resistance				0.38	$^\circ\text{C/W}$

The following table shows the body diode ratings and characteristics of MSC70SM120JCU2 device.

Table 4 • Body Diode Ratings and Characteristics

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	$V_{GS} = 0\text{ V}$ $I_{SD} = 40\text{ A}$		4		V
		$V_{GS} = -5\text{ V}$ $I_{SD} = 40\text{ A}$		4.2		
t_{rr}	Reverse recovery time	$I_{SD} = 40\text{ A}$ $V_{GS} = -5\text{ V}$ $V_R = 800\text{ V}$ $di_f/dt = 1000\text{ A}/\mu\text{s}$		90		ns
Q_{rr}	Reverse recovery charge			550		nC
I_{rr}	Reverse recovery current				13.5	

3.2 SiC Chopper Diode Ratings and Characteristics

The following table shows the SiC chopper diode ratings and characteristics of MSC70SM120JCU2 device.

Table 5 • SiC Chopper Diode Ratings and Characteristics

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Peak repetitive reverse voltage				1200	V
I_{RM}	Reverse leakage current	$V_R = 1200$ V	$T_J = 25$ °C	15	400	μ A
			$T_J = 175$ °C	250		
I_F	DC forward current		$T_C = 100$ °C	50		A
V_F	Diode forward voltage	$I_F = 50$ A	$T_J = 25$ °C	1.5	1.8	V
			$T_J = 175$ °C	2.1		
Q_C	Total capacitive charge	$V_R = 600$ V		224		nC
C	Total capacitance	$f = 1$ MHz, $V_R = 400$ V		246		pF
		$f = 1$ MHz, $V_R = 800$ V		182		
R_{thJC}	Junction-to-case thermal resistance				0.56	°C/W

3.3 Thermal and Package Characteristics

The following table shows the thermal and package characteristics of MSC70SM120JCU2 device.

Table 6 • Thermal and Package Characteristics

Symbol	Characteristics	Min	Typ	Max	Unit
V_{ISOL}	RMS isolation voltage, any terminal to case $t = 1$ min, 50/60 Hz	2500			V
T_{STG}	Storage temperature range	-55		175	°C
T_J	Operating junction temperature range	-55		175	
T_{JOP}	Recommended junction temperature under switching conditions	-55		$T_{Jmax} - 25$	
Torque	Terminals and mounting screws			1.1	N.m
Wt	Package weight		29.2		g

3.4 SiC MOSFET Performance Curves

The following images show the SiC MOSFET performance curves of the MSC70SM120JCU2 device.

Figure 3 • Maximum Thermal Impedance

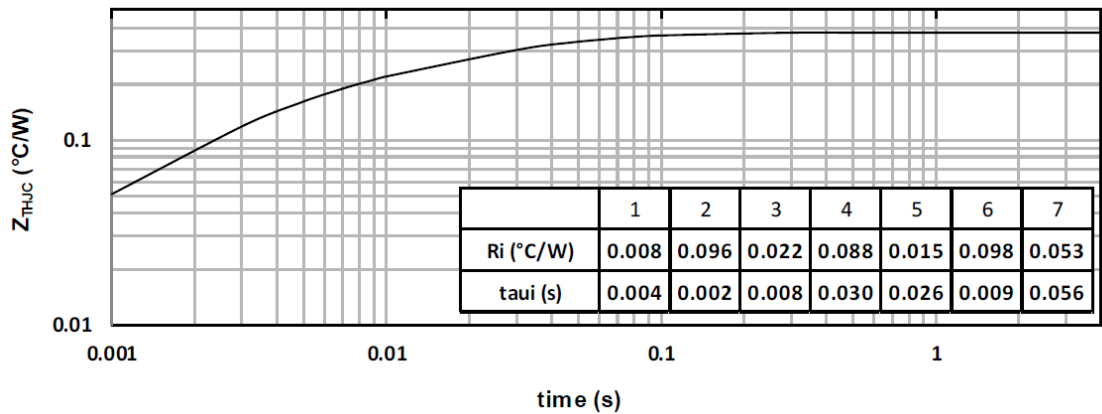


Figure 4 • Output Characteristics, $T_J=25^\circ\text{C}$

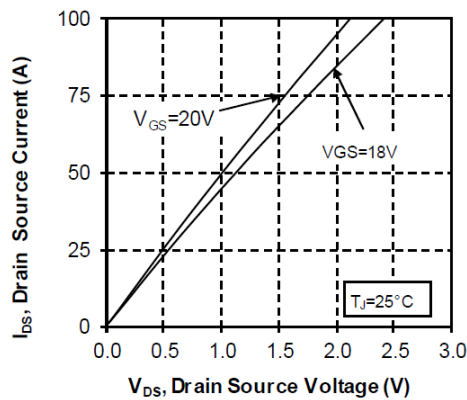


Figure 5 • Output Characteristics, $T_J=175^\circ\text{C}$

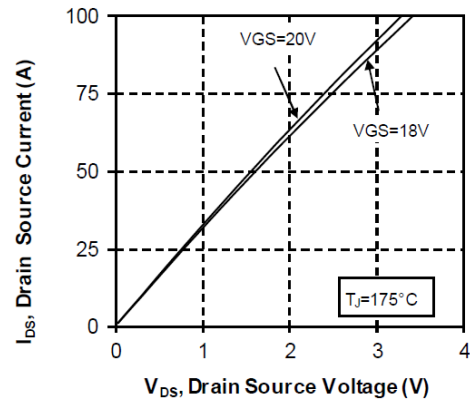


Figure 6 • Normalized $R_{DS(on)}$ vs. Temperature

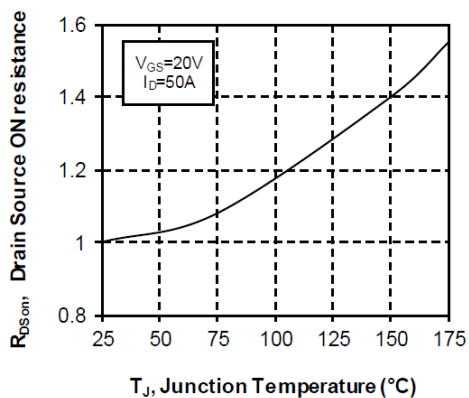


Figure 7 • Transfer Characteristics

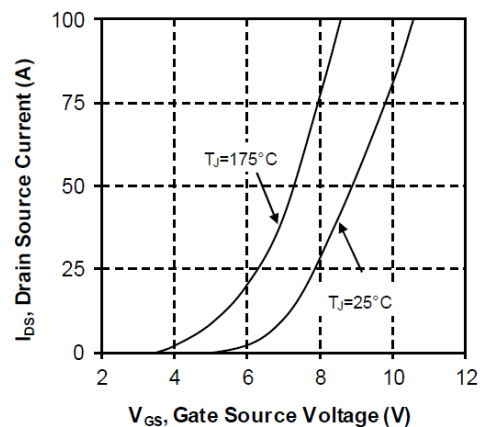


Figure 8 • Switching Energy vs. Rg

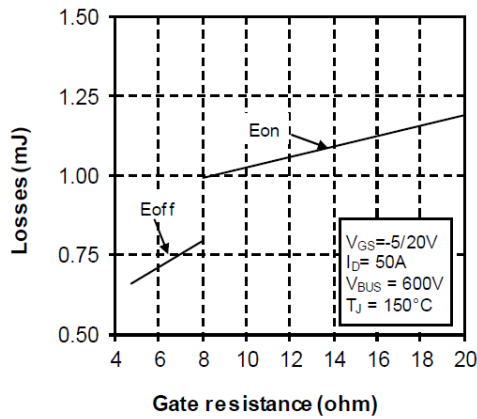


Figure 9 • Switching Energy vs. Current

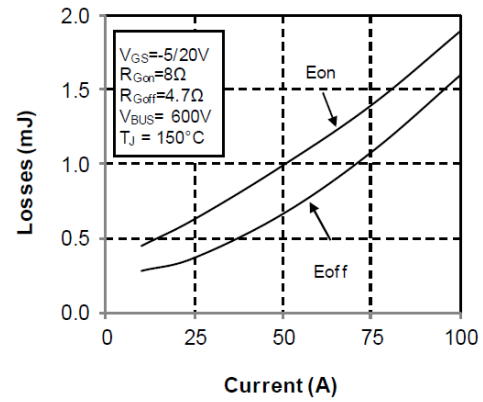


Figure 10 • Capacitance vs. Drain Source Voltage

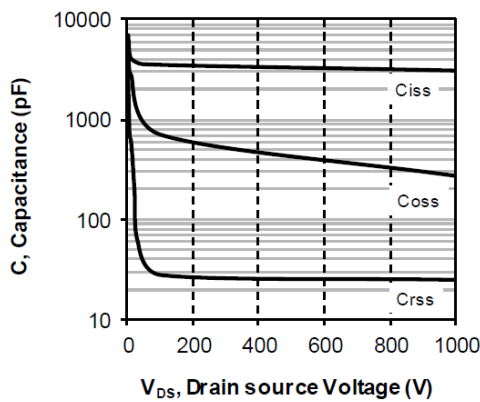


Figure 11 • Gate Charge vs. Gate Source Voltage

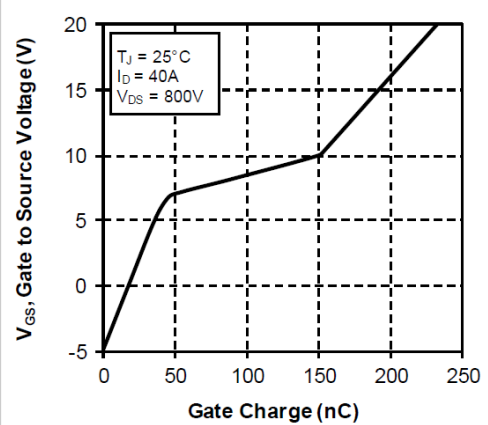


Figure 12 • Body Diode Characteristics, TJ=25 °C

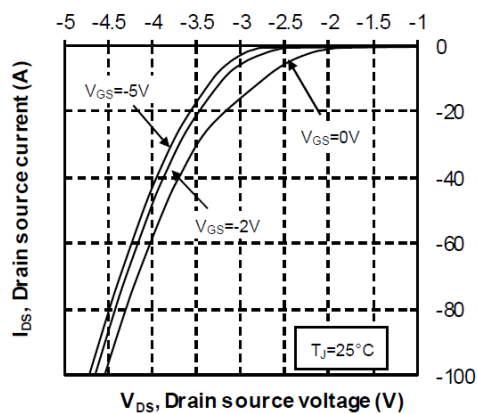


Figure 13 • 3rd Quadrant Characteristics, TJ=25 °C

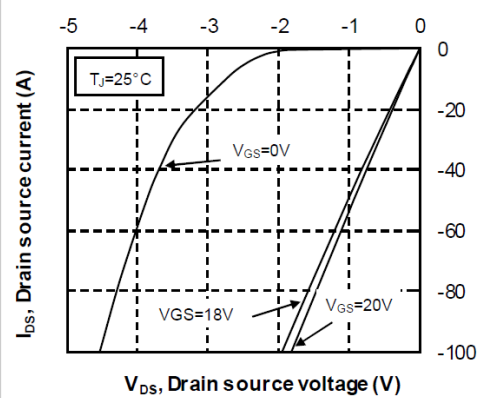


Figure 14 • Body Diode Characteristics, $T_J=175^\circ\text{C}$

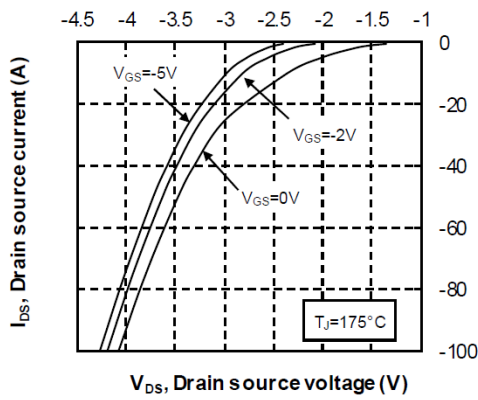


Figure 15 • 3rd Quadrant Characteristics, $T_J=175^\circ\text{C}$

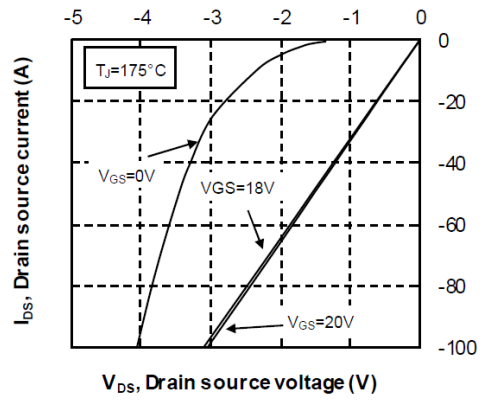
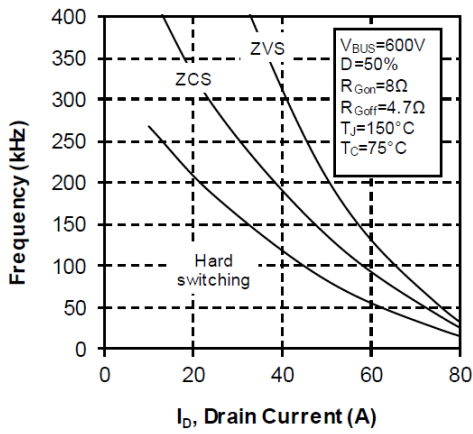


Figure 16 • Operating Frequency vs. Drain Current



3.5 SiC Diode Performance Curves

The following images show the SiC diode performance curves of MSC70SM120JCU2 device.

Figure 17 • Maximum Thermal Impedance

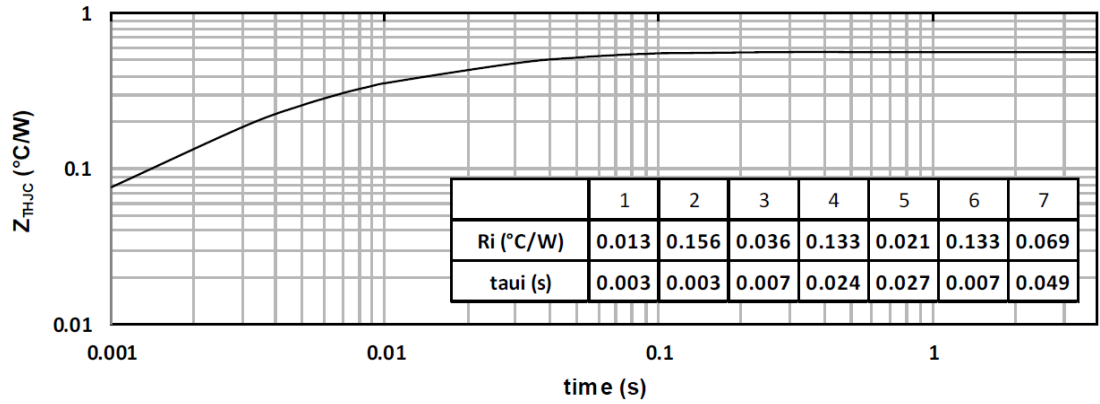


Figure 18 • Forward Characteristics

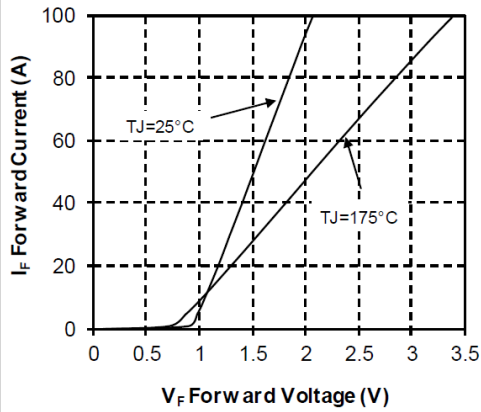
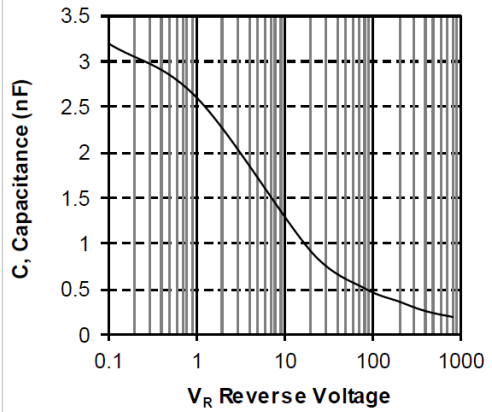


Figure 19 • Capacitance vs. Reverse Voltage



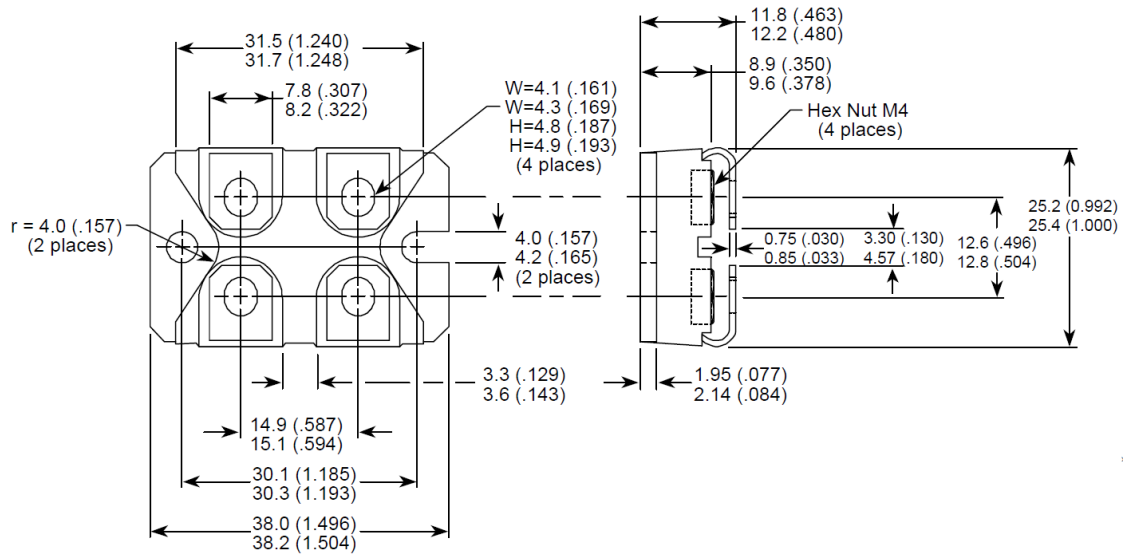
4 Package Specifications

The following section shows the package specification of MSC70SM120JCU2 device.

4.1 Package Outline Drawing

The following image illustrates the package outline drawing of MSC70SM120JCU2 device. The dimensions are in millimeters and (inches).

Figure 20 • Package Outline Drawing



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[T512F-YEB](#) [T513F](#) [T514F](#) [T554](#) [T612FSE](#) [25.161.3453.0](#) [25.179.2253.0](#) [25.194.3253.0](#) [25.325.1253.1](#) [25.326.4253.1](#) [25.330.0953.1](#)
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